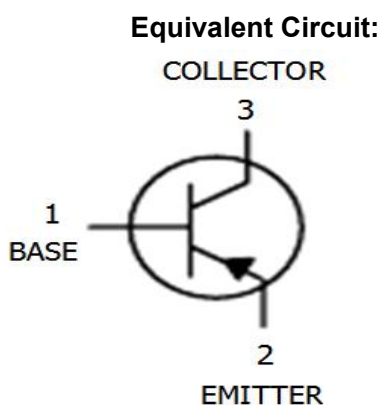


BC856

BC857

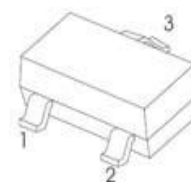
BC858

TRANSISTOR (PNP)



SOT-23

1.BASE
2.EMITTER
3.COLLECTOR



FEATURES:

- ※ Ideally suited for automatic insertion
- ※ For switching and AF amplifier applications

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	VCBO	-80	V
BC856		-50	
BC857		-30	
BC858			
Collector-Emitter Voltage	VCEO	-65	V
BC856		-45	
BC857		-30	
BC858			
Emitter-Base Voltage	VEBO	-5	V
Collector Current	IC	-0.1	A
Collector Power Dissipation	PC	200	mW
Thermal Resistance From Junction To Ambient	RθJA	625	°C/W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-65~+150	°C

DEVICE MARKING:

BC856A=3A; BC856B=3B

BC857A=3E; BC857B=3F; BC857C=3G

BC858A=3J; BC858B=3K; BC858C=3L


ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage BC856 BC857 BC858	V(BR)CBO	IC= -10μA, IE=0	-80 -50 -30			V
Collector-emitter breakdown voltage BC856 BC857 BC858	V(BR)CEO	IC= -10mA, IB=0	-65 -45 -30			V
Emitter-base breakdown voltage	V(BR)EBO	IE=-1μA, IC=0	-5			V
Collector cut-off current BC856 BC857 BC858	ICBO	VCB=-70 V , IE=0 VCB=-50 V , IE=0 VCB=-30 V , IE=0			-0.1	μA
Emitter cut-off current	IEBO	VEB=-5V , IC=0			-0.1	μA
DC current gain BC856A; 845A; 858A BC856B; 857B; 858B BC857C; BC858C	hFE	VCE=-5V, IC= -2mA	125 220 420		250 475 800	
Collector-emitter saturation voltage	VCE(sat)	IC=-100 mA, IB= -5mA			-0.5	V
Base-emitter saturation voltage	VBE(sat)	IC=-100 mA, IB= -5mA			-1.1	V
Transition frequency	fT	VCE=-5V, IC= -10mA f=100MHz	100			MHz
Collector Current Capacitance	Cob	VCE=-10V, f=1MHz			4.5	pF

CLASSIFICATION OF hFE

Rank	L	H	J
Range	125-200	200-350	300-400

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

